

### General Description

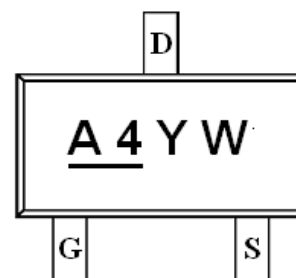
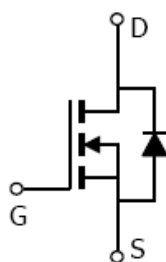
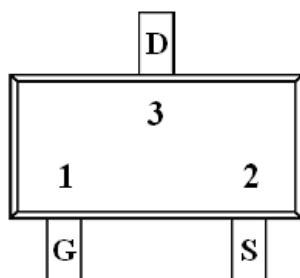
AFN3404AS, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

### Features

- $I_D=5.0A, R_{DS(ON)}=28m\Omega@V_{GS}=10V$
- $I_D=4.0A, R_{DS(ON)}=30m\Omega@V_{GS}=4.5V$
- $I_D=2.5A, R_{DS(ON)}=34m\Omega@V_{GS}=2.5V$
- $I_D=1.5A, R_{DS(ON)}=52m\Omega@V_{GS}=1.8V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- SOT-23 package design

### Pin Description ( SOT-23 )



### Application

- DC/DC Converters, High Speed Switching

### Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

### Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN3404ASS23RG	A4YW	SOT-23	Tape & Reel	3000 EA

- ※ A4 parts code
- ※ Y year code ( 0 ~ 9 )
- ※ W week code ( A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52 )
- ※ AFN3404ASS23RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



**Absolute Maximum Ratings**

( $T_A=25^{\circ}\text{C}$  Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	30	V
Gate –Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current( $T_J=150^{\circ}\text{C}$ )	$I_D$	$T_A=25^{\circ}\text{C}$	5.5
		$T_A=70^{\circ}\text{C}$	4.4
Pulsed Drain Current	$I_{DM}$	25	A
Continuous Source Current(Diode Conduction)	$I_S$	1.5	A
Power Dissipation	$P_D$	$T_A=25^{\circ}\text{C}$	1.25
		$T_A=70^{\circ}\text{C}$	0.8
Operating Junction Temperature	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	-55/150	$^{\circ}\text{C}$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^{\circ}\text{C/W}$

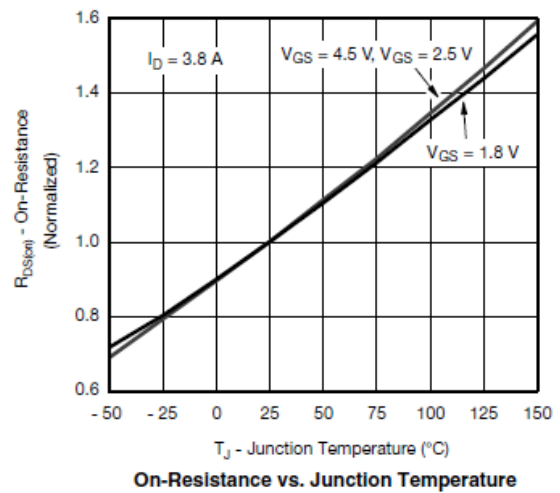
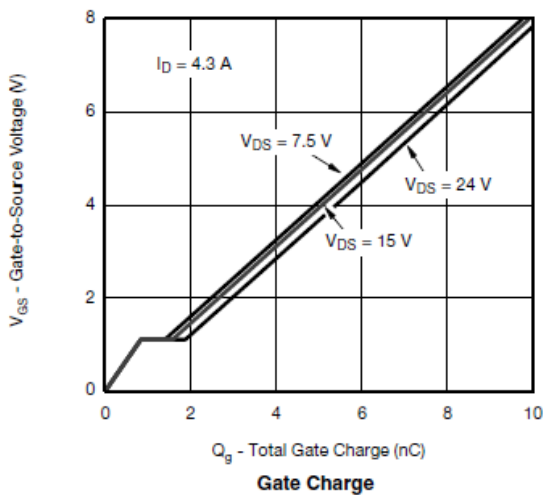
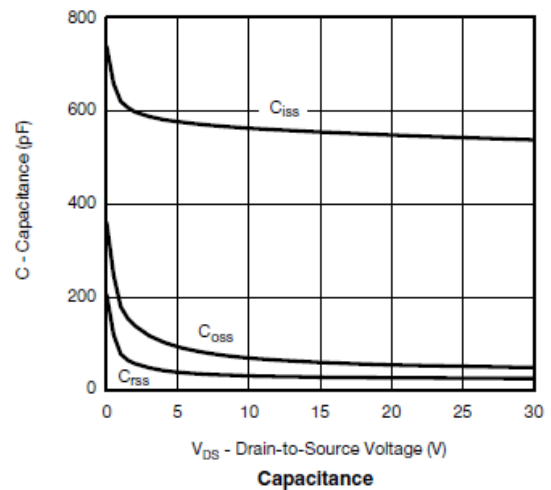
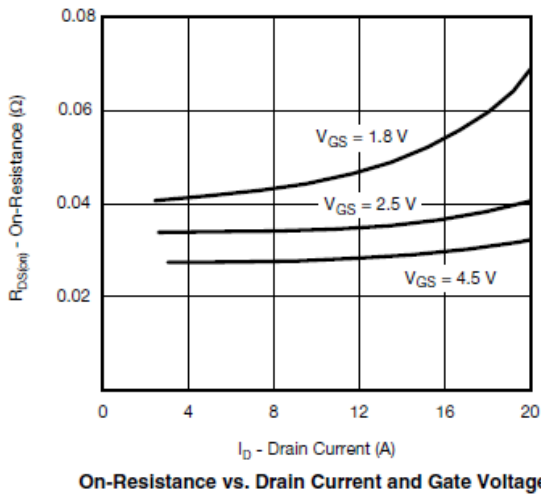
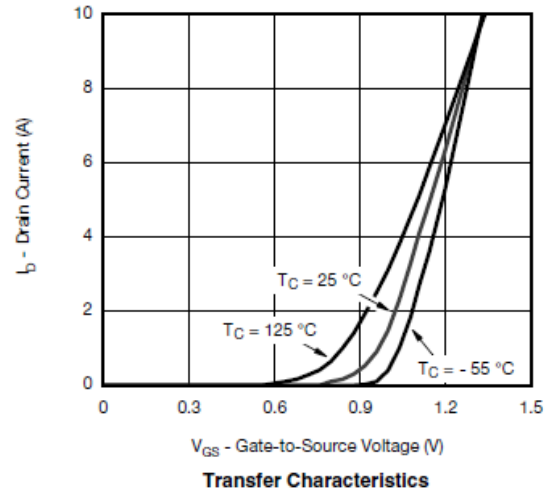
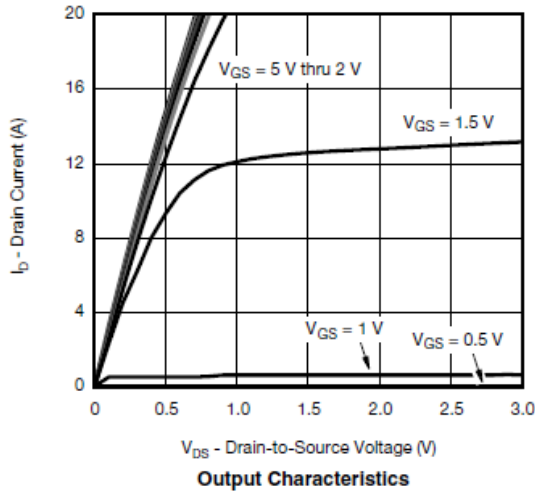
**Electrical Characteristics**

( $T_A=25^{\circ}\text{C}$  Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.6		1.1	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 16V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=24V, V_{GS}=0V$			1	uA
		$V_{DS}=24V, V_{GS}=0V$ $T_J=85^{\circ}\text{C}$			30	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS}=10V$	10			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=5.0A$		23	28	m $\Omega$
		$V_{GS}=4.5V, I_D=4.0A$		25	30	
		$V_{GS}=2.5V, I_D=2.5A$		28	34	
		$V_{GS}=1.8V, I_D=1.5A$		45	52	
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=3.8A$		30		S
Diode Forward Voltage	$V_{SD}$	$I_S=1.0A, V_{GS}=0V$		0.8	1.3	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=15V, V_{GS}=4.5V$ $I_D \geq 3.4A$		6	10	nC
Gate-Source Charge	$Q_{gs}$			1.0		
Gate-Drain Charge	$Q_{gd}$			0.8		
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V$ $f=1\text{MHz}$		570		pF
Output Capacitance	$C_{oss}$			60		
Reverse Transfer Capacitance	$C_{rss}$			30		
Turn-On Time	$t_{d(on)}$	$V_{DD}=15V, R_L=4.3\Omega$ $I_D \geq 3.5A, V_{GEN}=4.5V$ $R_G=1\Omega$		6	12	ns
	$t_r$			10	20	
Turn-Off Time	$t_{d(off)}$			20	40	
	$t_f$			10	20	

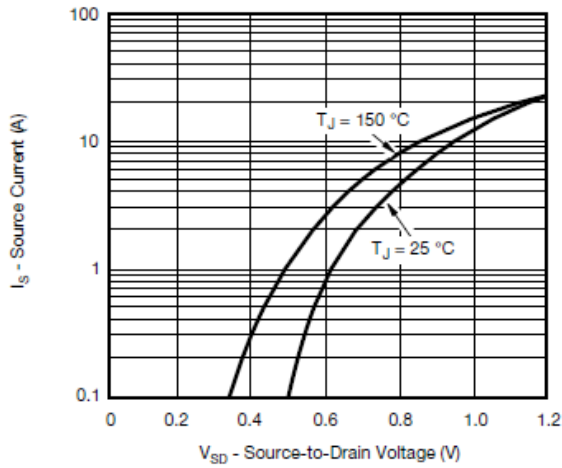


## Typical Characteristics

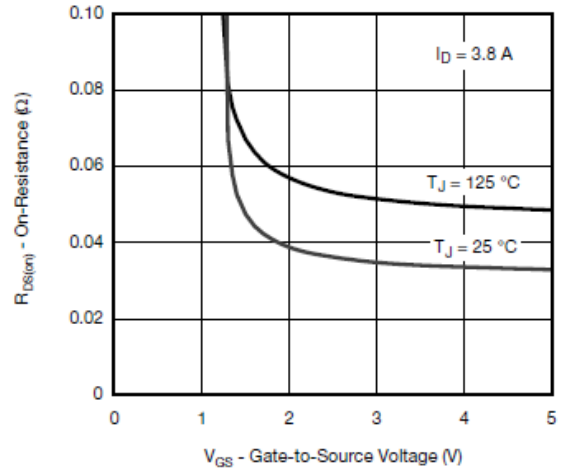




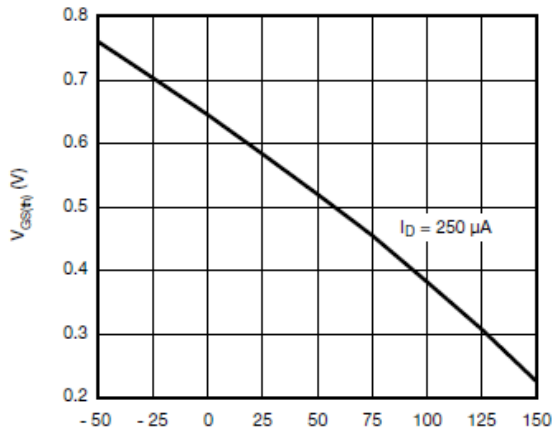
## Typical Characteristics



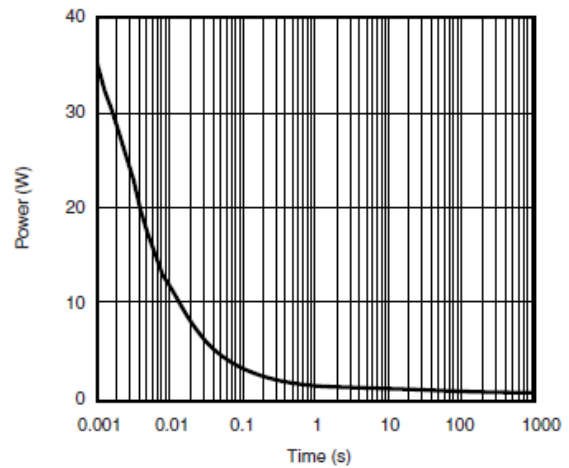
Source-Drain Diode Forward Voltage



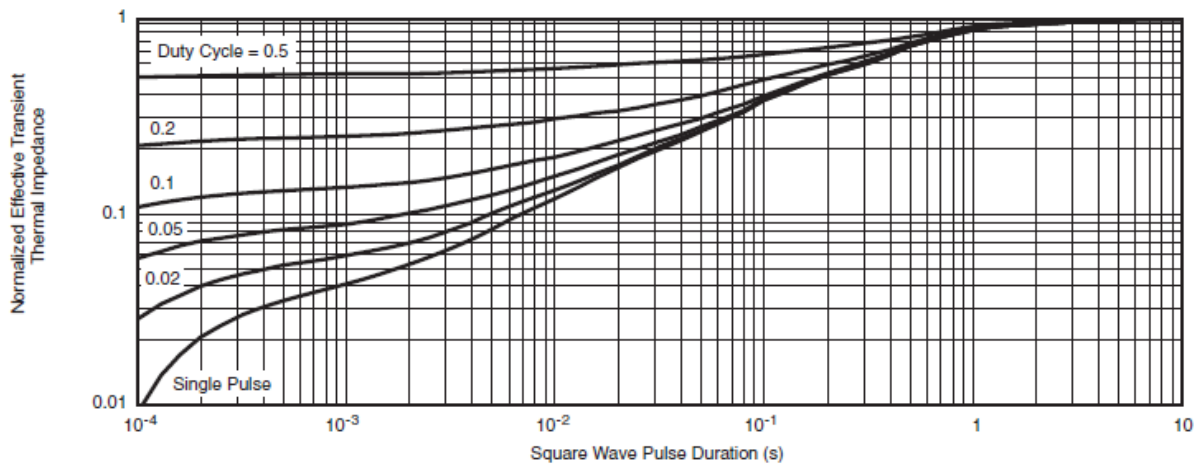
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Foot



**Typical Characteristics**

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

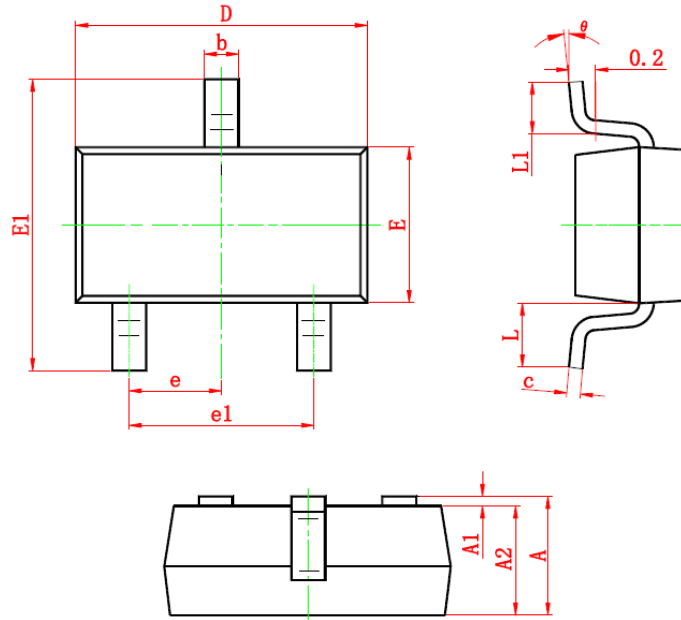


Unclamped Inductive Switching Test Circuit & Waveforms





**Package Information ( SOT-23 )**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°

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